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SLIDE I



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PERSPECTIVE:

ARYLAS

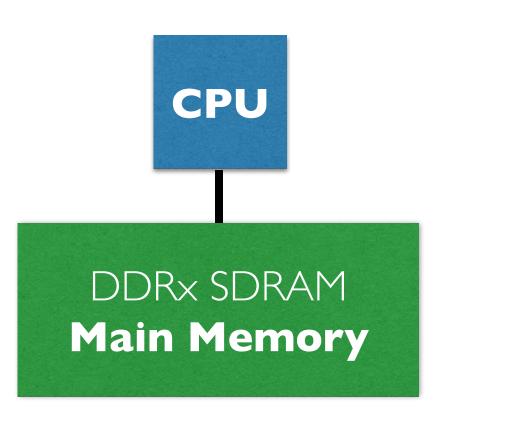
	Cost for	Power for	Power
	I0 GB	I0 GB	per GB/s
Off-Chip SRAM	\$1,000	0.4 W	0.2 W
DDR3 SDRAM	\$100		0.2 W
NAND Flash	\$10	0 W	3 W

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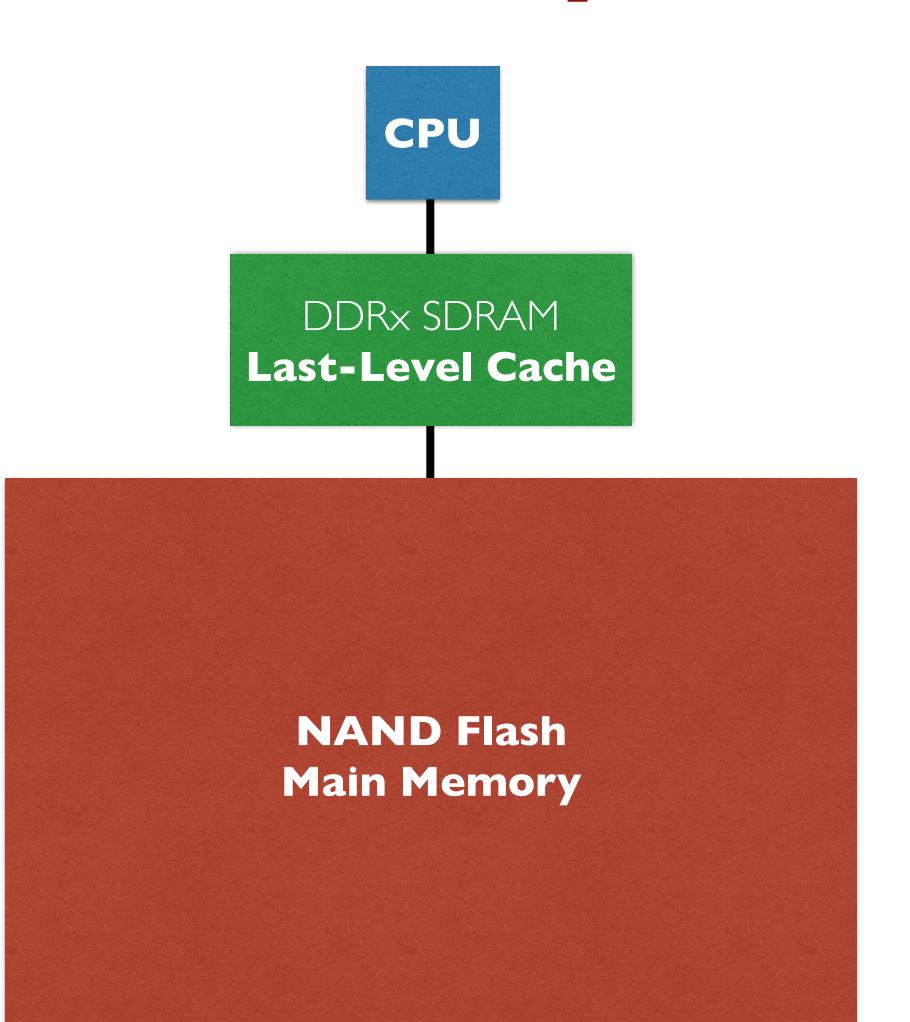
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SLIDE 2

Flash-Based Main Memory



Note: wear-out is mitigated by using MANY devices (thousands). A single device would wear out in under two days; therefore, 1000 devices should last for at least a year.

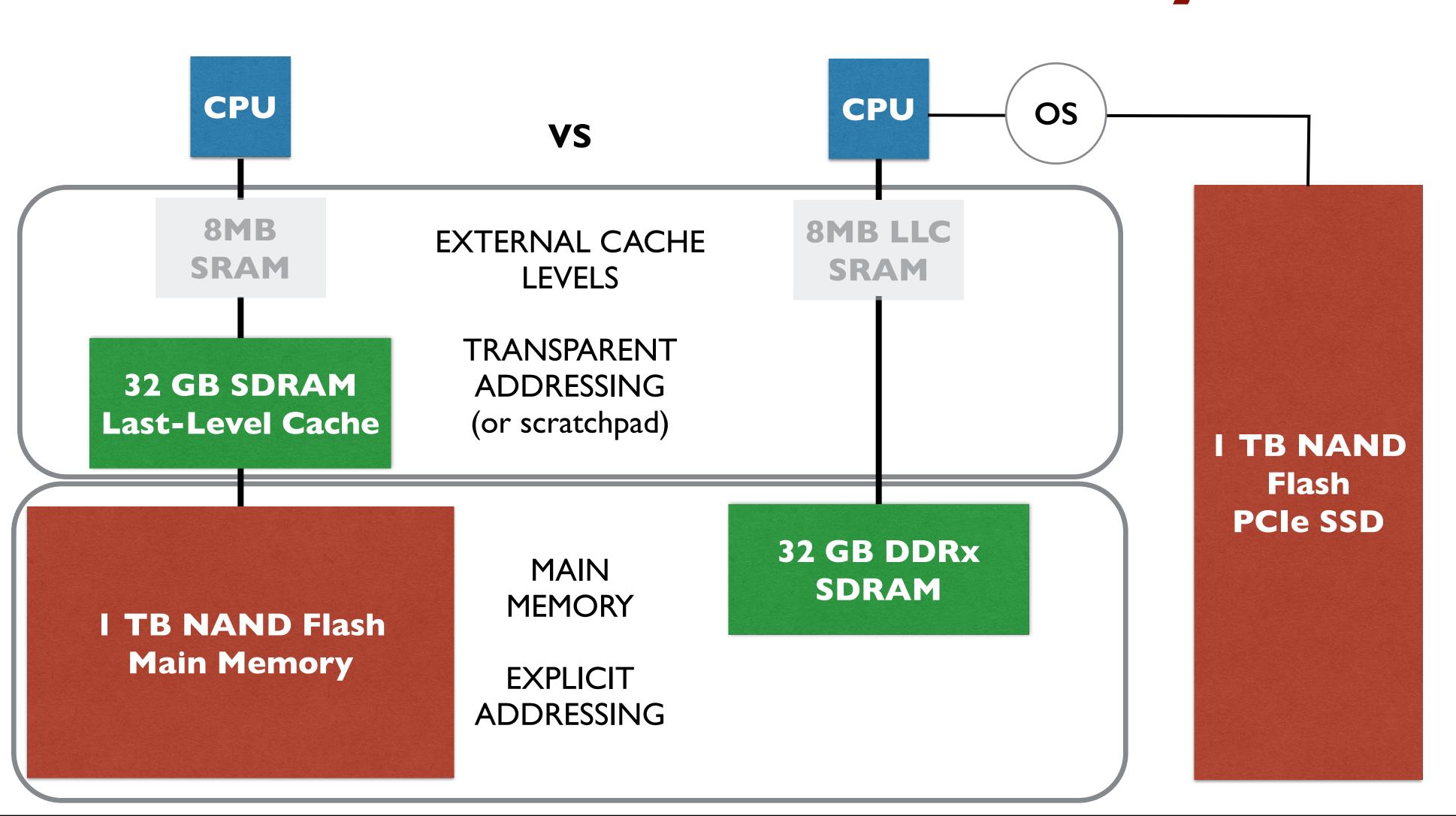


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SLIDE 3

Flash-Based Main Memory

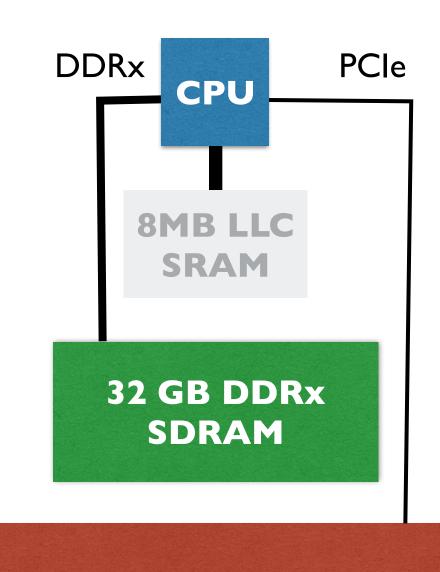


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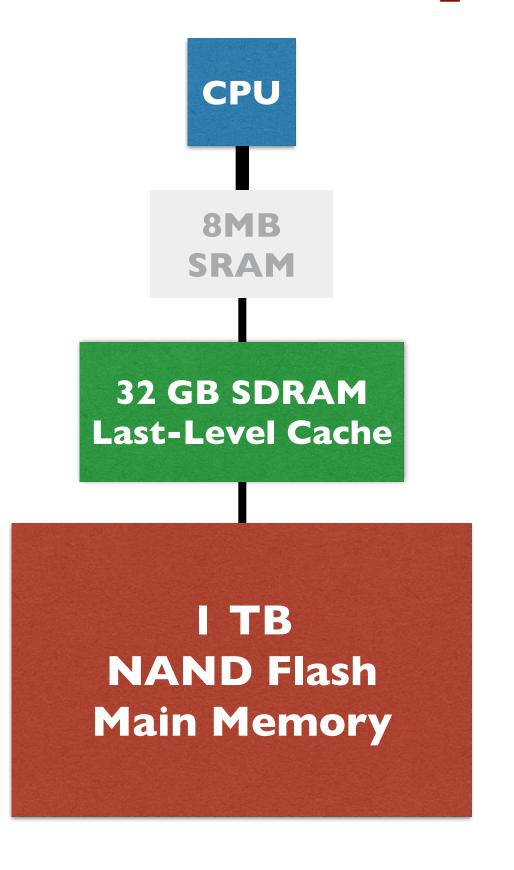
SLIDE 4

A Tale of 3 Memory Systems

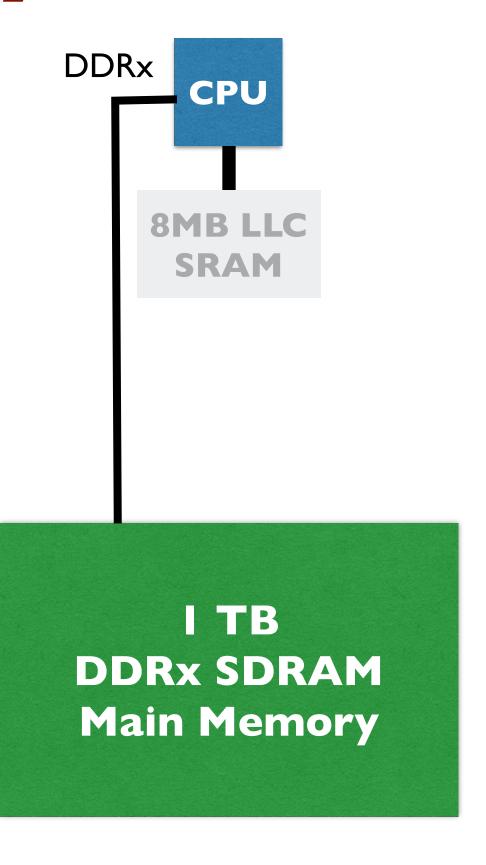


I TB
NAND Flash
PCIe SSD (I/O)

SSD \$500 – 10W



Hybrid \$500 - 10s of W

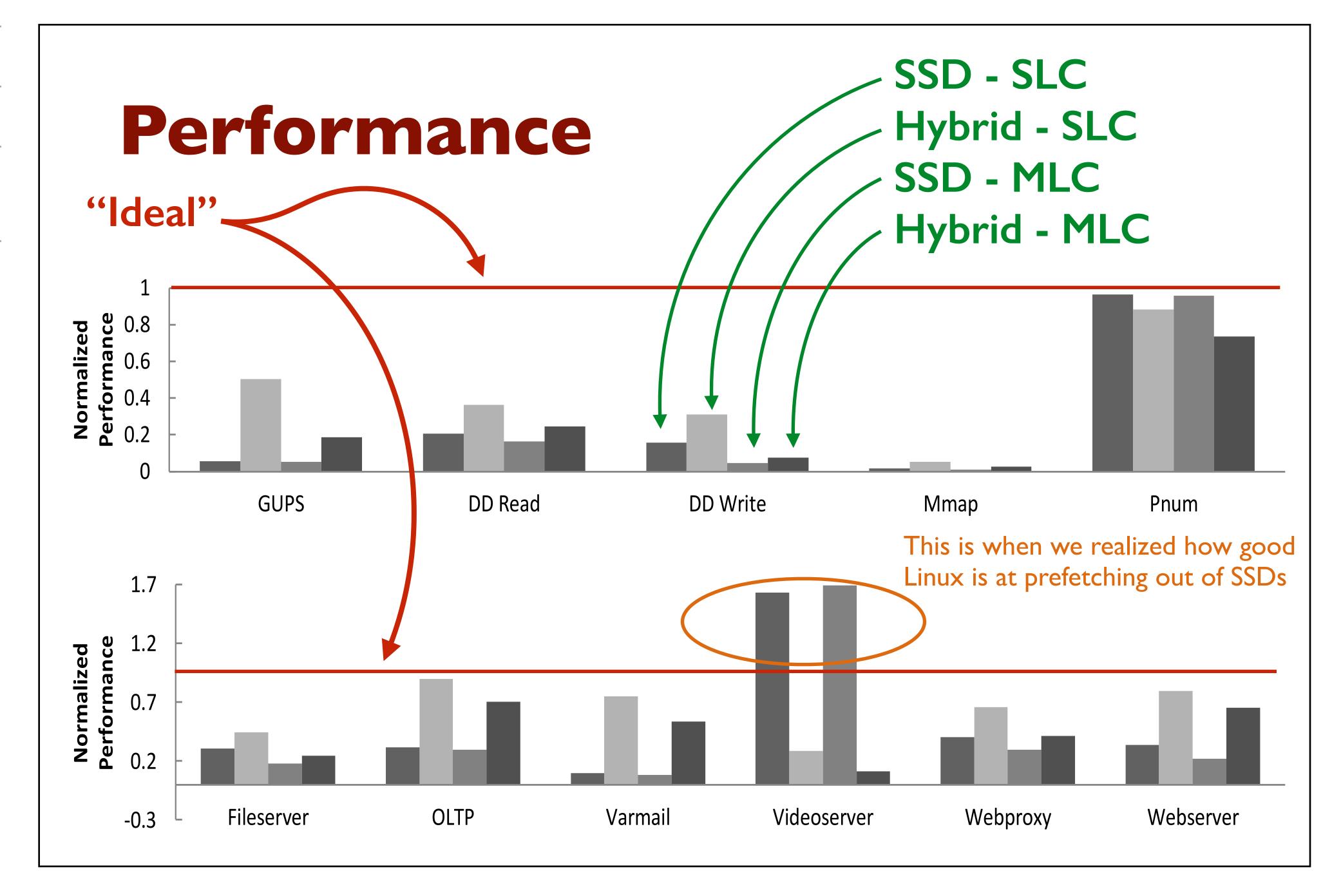


Ideal \$10,000 – 100W

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SLIDE 5



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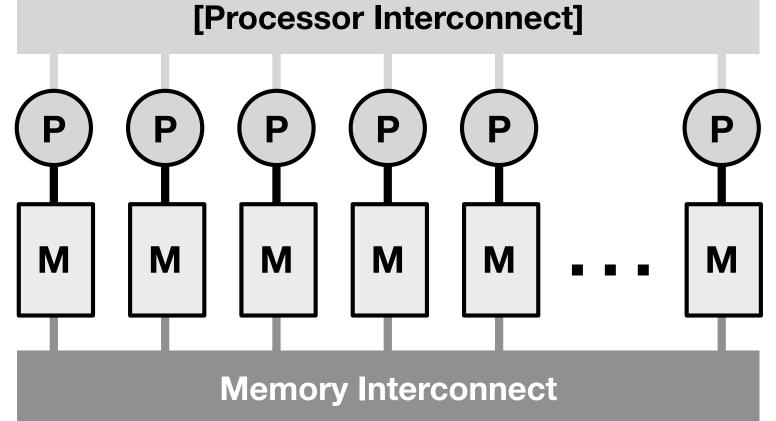
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SLIDE 6

Less Easily Quantified Stuff

Out of the box:

- Journaled main memory built-in checkpoint/repair (flash side-effect)
- No VM or TLB needed (flash maps self)
 If HMC-type intra-memory network used:
- · Global physical space
- · ... even virtual



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SLIDE 7



Bottom Line

Your future is non-volatile ... and BIG

- Less expensive
- Lower power
- Performance approaching that of DRAM
 Global address space for free

Checkpoint/repair built-in

What we need from you: BIG benchmarks